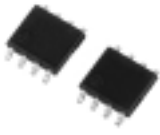


MITSUBISHI IGBT
CY20AAJ-8

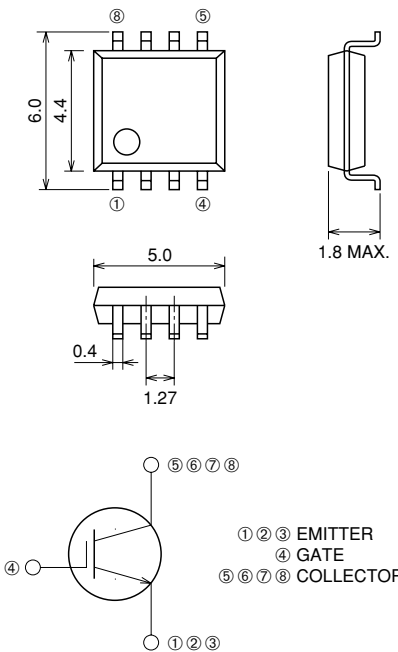
Nch IGBT for STROBE FLASHER

CY20AAJ-8



- VCES 400V
- ICM 130A
- Drive voltage 4V

OUTLINE DRAWING Dimensions in mm



SOP-8

APPLICATION

Strobe flasher for Camera

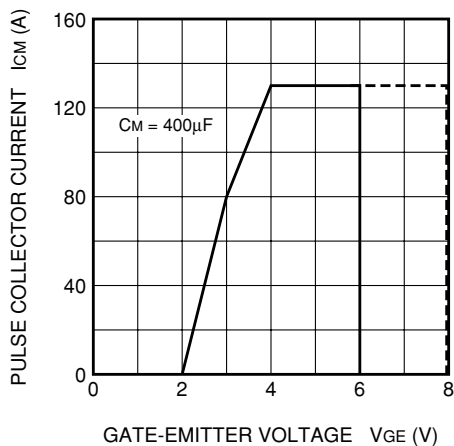
MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CE} S	Collector-emitter voltage	V _{GE} = 0V	400	V
V _{GE} S	Gate-emitter voltage	V _{CE} = 0V	±6	V
V _{GEM}	Peak gate-emitter voltage	V _{CE} = 0V, t _w = 10s	±8	V
I _{CM}	Collector current (Pulsed)	C _M = 400μF see figure1	130	A
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +150	°C

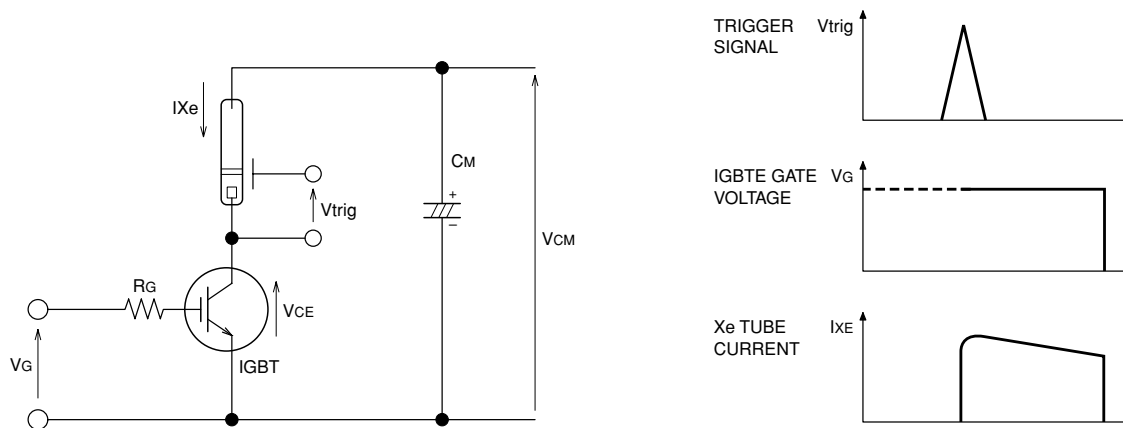
ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	IC = 1mA, VGE = 0V	450	—	—	V
ICES	Collector-emitter leakage current	VCE = 400V, VGE = 0V	—	—	10	μA
IGES	Gate-emitter leakage current	VGE = ±6V, VCE = 0V	—	—	±0.1	μA
VGE (th)	Gate-emitter threshold voltage	VCE = 10V, IC = 1mA	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE



Recommended operation conditions	Maximum operation conditions
VCM = 330V	VCM = 350V
ICP = 120A	ICP = 130A
CM = 300μF	CM = 400μF
VGE = 5V	

- Notice 1. Gate drive voltage during on-state must be applied to satisfy the rating of maximum pulse collector current. And peak reverse gate current during turn-off must become less than 0.1A. (In general, when RG (off) = 30Ω, it is satisfied.)
- Notice 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully not to give static electricity.
- Notice 3. The operation life should be endured 5,000 shots under the charge current (Ixe ≤ 130A : full luminescence condition) of main condenser (CM = 400μF). Repetitive period under the full luminescence conditions is over 3 seconds.
- Notice 4. Total gate operation time must be applied within 5,000 hours.